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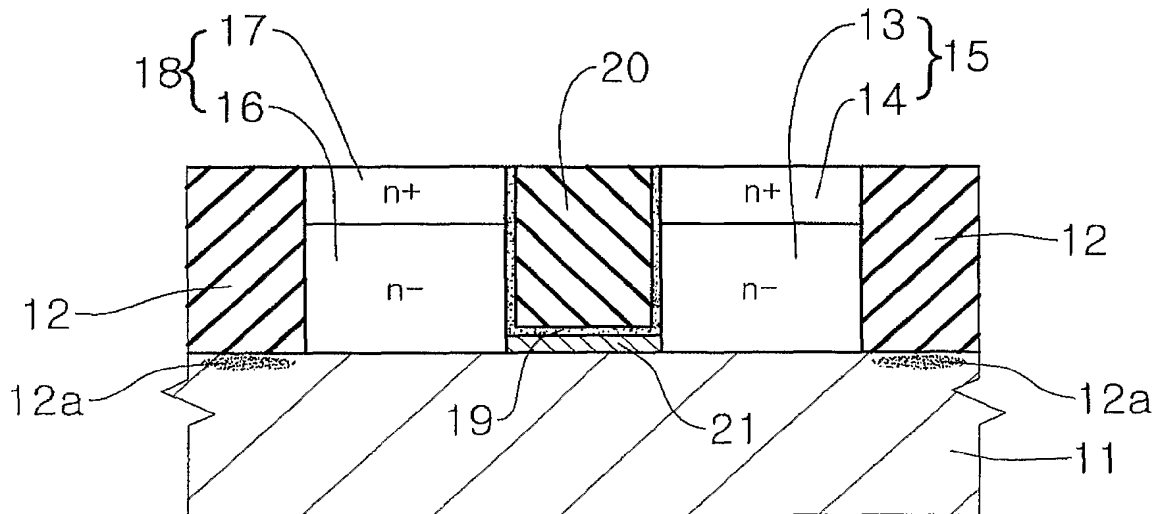
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**(54) Title:** SEMICONDUCTOR DEVICE OF HIGH BREAKDOWN VOLTAGE AND MANUFACTURING METHOD THEREOF



**(57) Abstract:** Disclosed are a semiconductor device of high breakdown voltage and a method manufacturing the same. According to the invention, it is possible to previously prevent an increase size of the device due to a separation of a high concentration impurity layer and a gate electrode pattern by embedding the gate electrode pattern in a bottom of a semiconductor substrate, and sequentially stacking a low concentration impurity layer and a high concentration impurity layer for source/drain diffusion layers on both sides of the gate electrode pattern, thereby allowing the high concentration impurity layer to easily secure a voltage drop areas necessary for itself without being spaced from the gate electrode pattern.